UG1A - UG1D

ULTRAFAST EFFICIENT PLASTIC SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 200V CURRENT: 1.0 A

Features

- Low power loss
- High surge capability
- Glass passivated chip junction
- Ultra-fast recovery time for high efficiency
- High temperature soldering guaranteed
 250°C/10sec/0.375" lead length at 5 lbs tension

Mechanical Data

Case: D O - 4 1 Molded Plastic

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

Polarity: Cathode Band

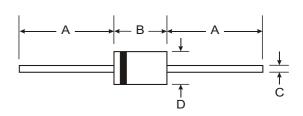
Weight: 0.34 grams (approx.)

Mounting Position: Any

Marking: Type Number







DO-41					
Dim	Min	Max			
Α	25.40	_			
В	4.06	5.21			
С	0.71	0.864			
D	2.00	2.72			
All Dimensions in mm					

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	UG1A	UG1B	UG1C	UG1D	Unit
Maximum Recurrent Peak Reverse Voltage	Vrrm	50	100	150	200	V
Maximum RMS Voltage	Vrms	35	70	105	140	V
Maximum DC blocking Voltage	Vdc	50	100	150	200	V
Maximum Average Forward Rectified Current 3/8″ lead length at Ta =75℃	If(av)	1.0			А	
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load	Ifsm	40.0			А	
Maximum Forward Voltage at Forward current 1A Peak	Vf	0.95			V	
Maximum DC Reverse Current Ta =25°C	lr	5.0			μА	
at rated DC blocking voltage Ta =125℃		200.0			μА	
Maximum Reverse Recovery Time (Note 1)	Trr	15			nS	
Typical Junction Capacitance (Note 2)	Cj	7.0			pF	
Typical Thermal Resistance (Note 3)	R(ja)	60.0			°C/W	
Storage and Operating Junction Temperature	Tstg,Tj	-55 to +150		$^{\circ}$		

Note:

- 1. Reverse Recovery Condition If = 0.5A, Ir =1.0A, Irr =0.25A
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 3. Thermal Resistance from Junction to Ambient at 3/8 " lead length, P.C. Board Mounted



RATINGS AND CHARACTERISTIC CURVES UG1A THRU UG1D

